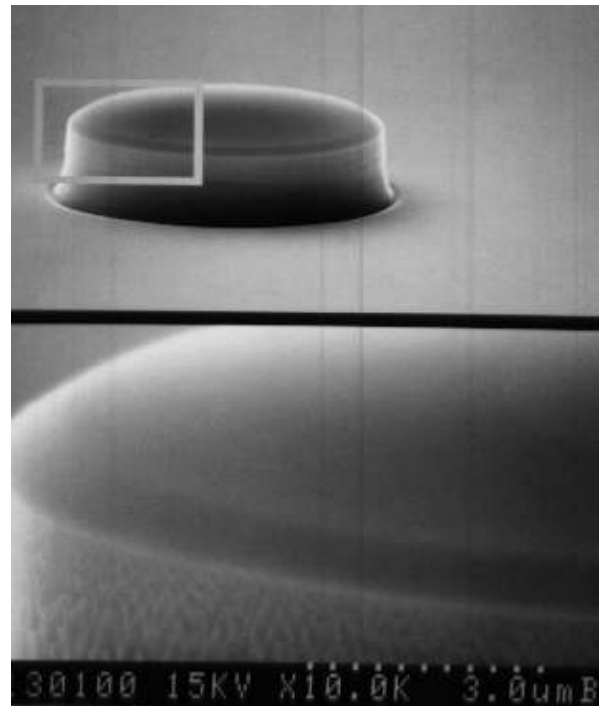
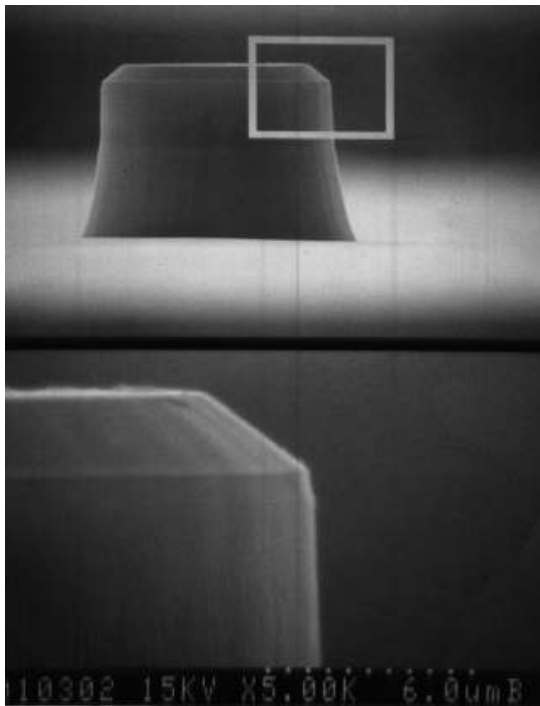


Plasmalab Data

ICP - RIE of InP/ InGaAsP

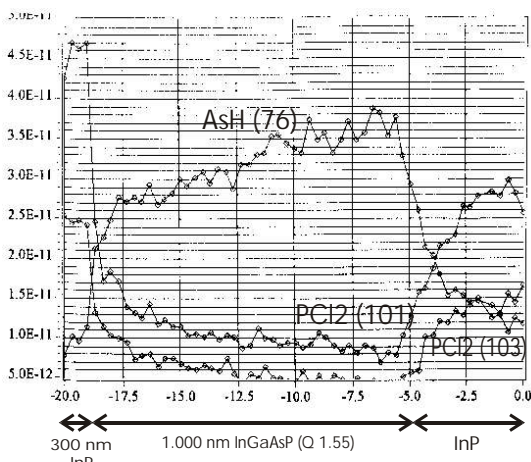


Courtesy of Infineon Munich, ZFE T KM 3 (Dr. ...)

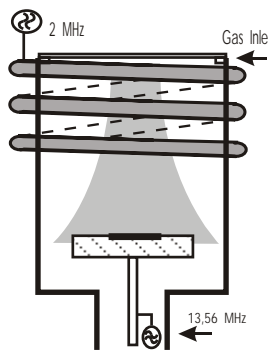
Plasmalab System 100

Plasmalab System 133

Plasmalab 80 Plus



*In situ
 mass spectrometry*



Technology:

Inductive Coupled Plasma ICP - RIE*
 13.56 MHz driven electrode
 Cl based process

*original work by ECR, see:
http://www.oxfordplasma.de/technols/rie_ecr.htm

Results:

2.5 μm deep, anisotropic Etch (Al_2O_3 mask)
 1.5 μm deep, anisotropic Etch (Si_3N_4 mask)
 Rates: 100 nm/ min in InP
 Selectivity In : InGaAsP 1 : 1
 Uniformity over 3": $\leq \pm 3\%$